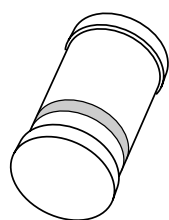


DATA SHEET



BAS32L High-speed diode

Product specification
Supersedes data of 1996 Sep 10

2002 Jan 23

High-speed diode

BAS32L

FEATURES

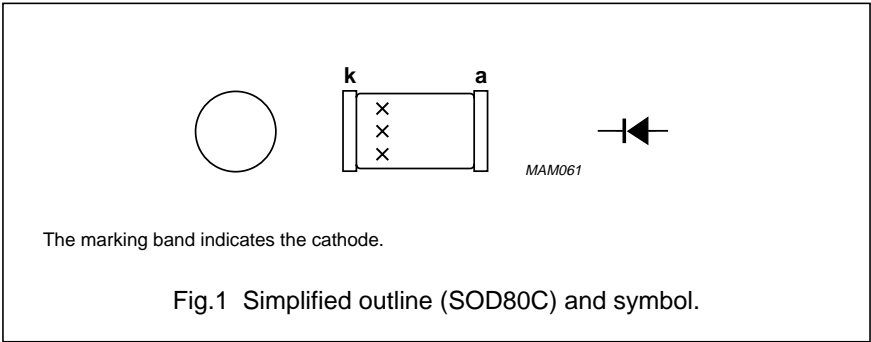
- Small hermetically sealed glass SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

- High-speed switching
- Fast logic applications.

DESCRIPTION

The BAS32L is a high-speed switching diode fabricated in planar technology, and encapsulated in the small hermetically sealed glass SOD80C SMD package.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	100	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	see Fig.2; note 1	–	200	mA
I_{FRM}	repetitive peak forward current		–	450	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\text{ }\mu\text{s}$ $t = 1\text{ ms}$ $t = 1\text{ s}$	– – –	4 1 0.5	A A A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$; note 1	–	500	mW
T_{stg}	storage temperature		–65	+200	°C
T_j	junction temperature		–	200	°C

Note

1. Device mounted on an FR4 printed-circuit board.

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ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_F	forward voltage	see Fig.3 $I_F = 5\text{ mA}$ $I_F = 100\text{ mA}$ $I_F = 100\text{ mA}; T_j = 100\text{ }^{\circ}\text{C}$	620 – –	750 1000 930	mV mV mV
I_R	reverse current	see Fig.5 $V_R = 20\text{ V}$ $V_R = 75\text{ V}$ $V_R = 20\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$ $V_R = 75\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	– – – –	25 5 50 100	nA μA μA μA
$V_{(BR)R}$	reverse breakdown voltage	$I_R = 100\text{ }\mu\text{A}$	100	–	V
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0$; see Fig.6		2	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\text{ }\Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7		4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 50\text{ mA}$; $t_r = 20\text{ ns}$; see Fig.8	–	2.5	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		300	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	350	K/W

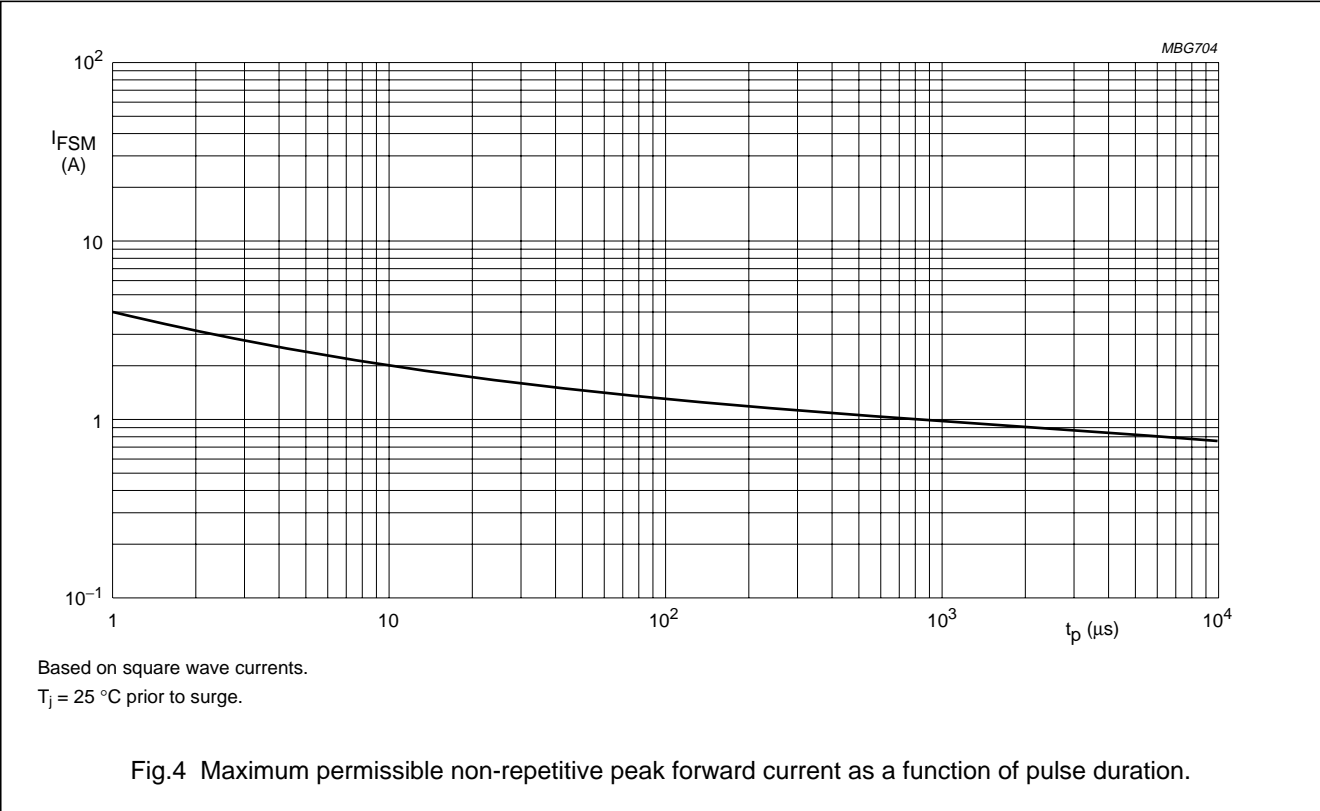
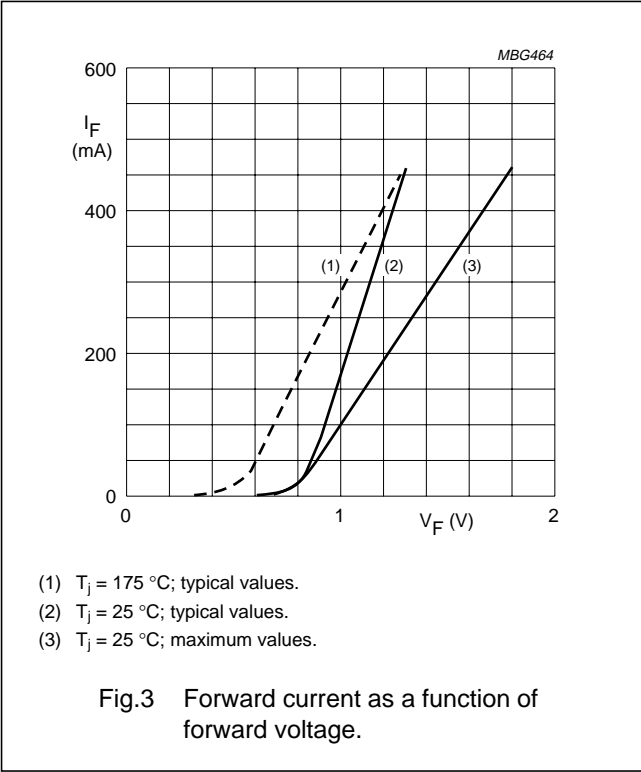
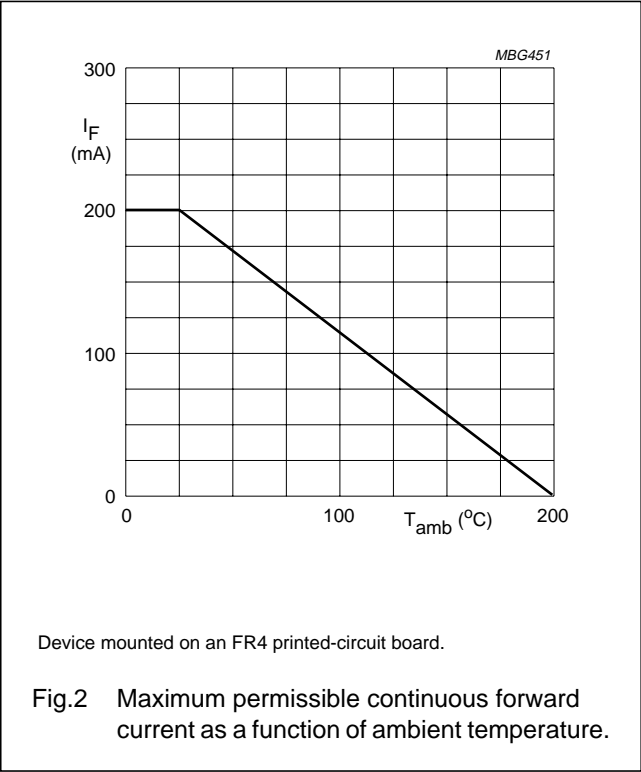
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed diode

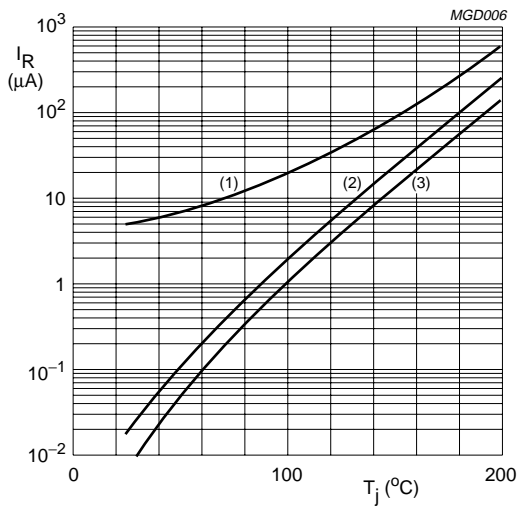
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GRAPHICAL DATA



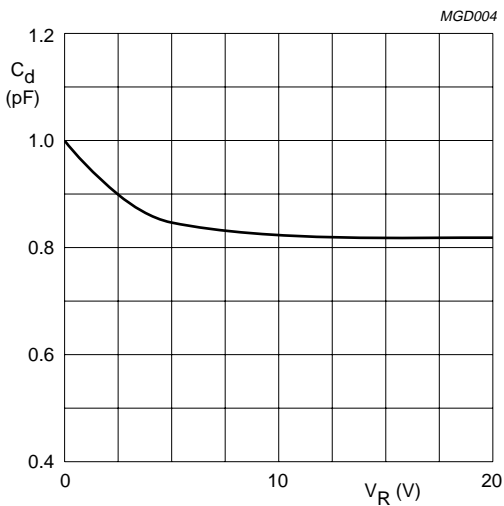
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- (1) $V_R = 75 V$; maximum values.
- (2) $V_R = 75 V$; typical values.
- (3) $V_R = 20 V$; typical values.

Fig.5 Reverse current as a function of junction temperature.

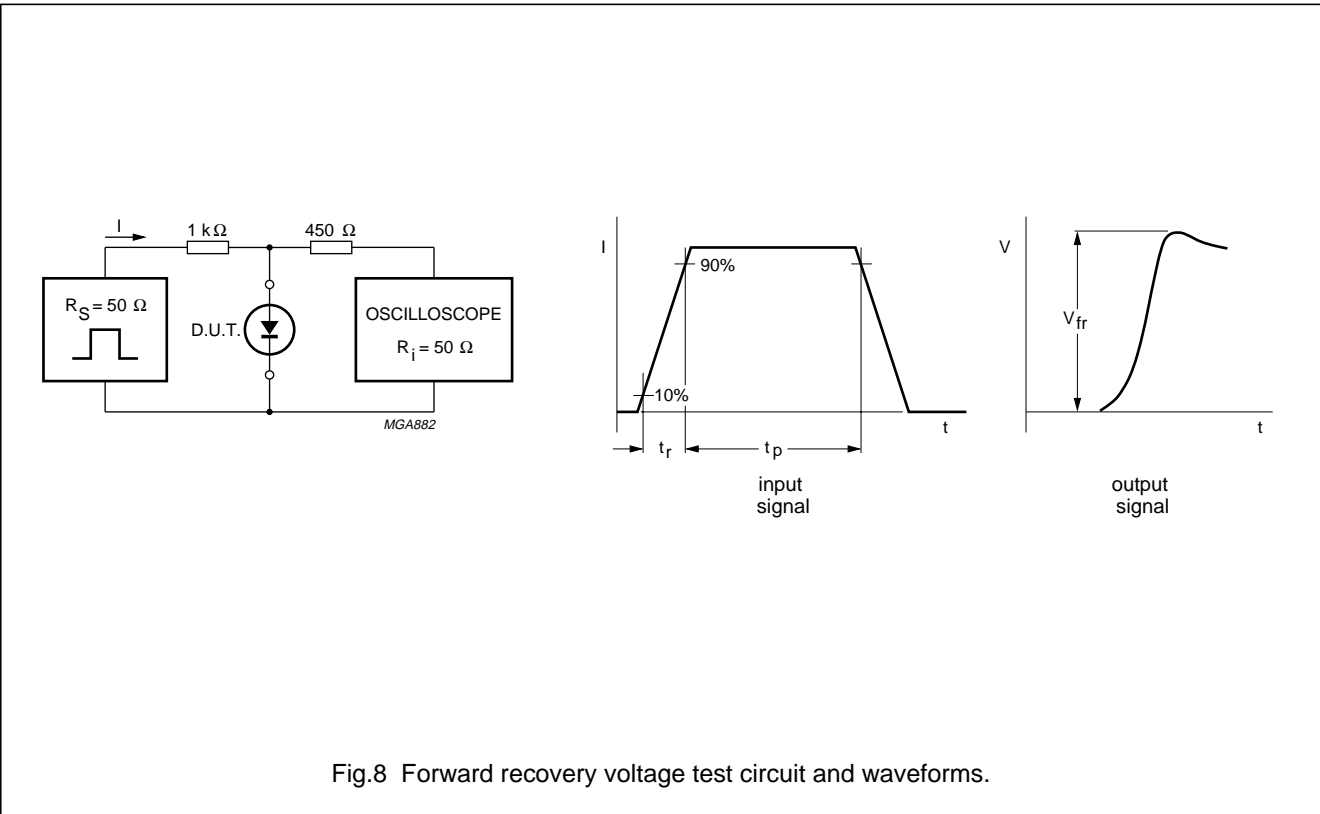
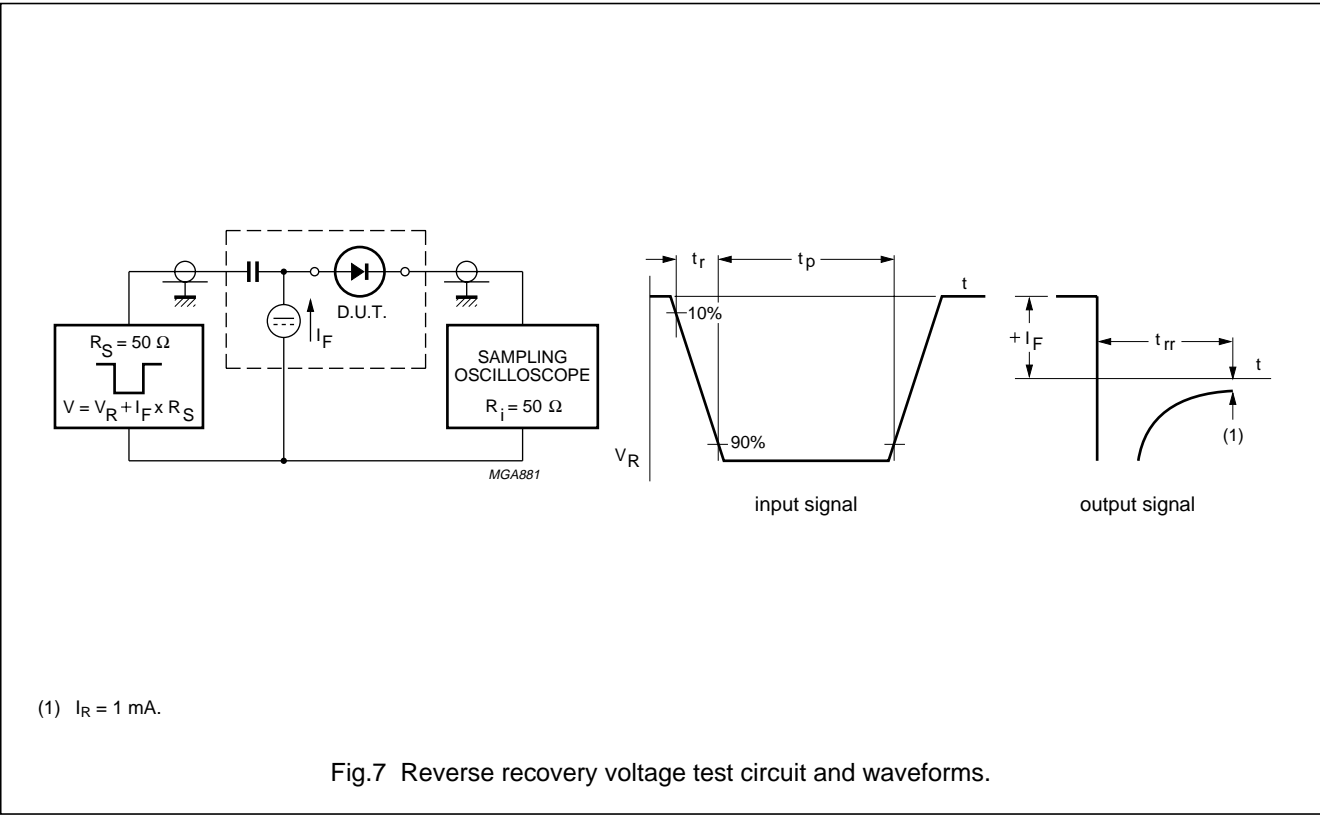


$f = 1 MHz$; $T_j = 25 ^{\circ}C$.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

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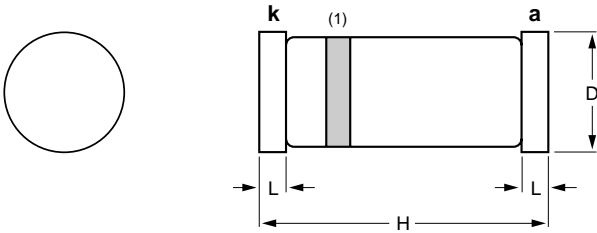
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PACKAGE OUTLINE

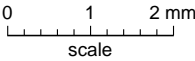
Hermetically sealed glass surface mounted package; 2 connectors

SOD80C



DIMENSIONS (mm are the original dimensions)

UNIT	D	H	L
mm	1.60 1.45	3.7 3.3	0.3



Note
 1. The marking band indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD80C	100H01					97-06-20

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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NOTES

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Contact information

For additional information please visit **<http://www.semiconductors.philips.com>**. Fax: **+31 40 27 24825**

For sales offices addresses send e-mail to: **sales.addresses@www.semiconductors.philips.com**.

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